

Features

- N-Channel, 5V Logic Level Control
- Enhancement mode
- Very low on-resistance $R_{DS(on)}$ @ $V_{GS}=4.5\text{ V}$
- Fast Switching
- 100% Avalanche Tested
- Pb-free lead plating; RoHS compliant

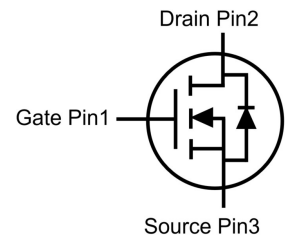
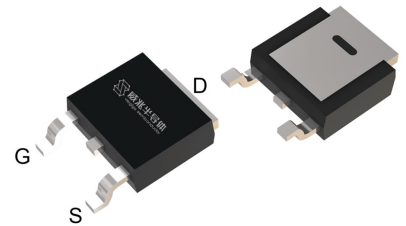


Halogen-Free

Part ID	Package Type	Marking	Packing
VS3698AD	TO-252	3698AD	2500pcs/Reel

V_{DS}	30	V
$R_{DS(on),TYP}@ V_{GS}=10\text{ V}$	3.1	mΩ
$R_{DS(on),TYP}@ V_{GS}=4.5\text{ V}$	4.5	mΩ
I_D	105	A

TO-252



Maximum ratings, at $T_J=25\text{ °C}$, unless otherwise specified

Symbol	Parameter	Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage	30	V
I_S	Diode continuous forward current	$T_C=25\text{ °C}$ 105	A
I_D	Continuous drain current@ $V_{GS}=10\text{ V}$	$T_C=25\text{ °C}$ 105	A
		$T_C=100\text{ °C}$ 68	A
I_{DM}	Pulse drain current tested ①	$T_C=25\text{ °C}$ 320	A
P_D	Maximum power dissipation	$T_C=25\text{ °C}$ 83	W
V_{GS}	Gate-Source voltage	±20	V
$T_{STG} T_J$	Storage and operating temperature range	-55 to 175	°C

Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	1.8	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	40	°C/W
Drain-Source Avalanche Ratings			
EAS	Avalanche Energy, Single Pulsed ②	256	mJ

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ $T_j=25^{\circ}\text{C}$ (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V$	--	--	1	μA
	Zero Gate Voltage Drain Current($T_j=125^{\circ}\text{C}$)	$V_{DS}=30V, V_{GS}=0V$	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	--	--	± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.8	2.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance③	$V_{GS}=10V, I_D=20A$	--	3.1	4.5	m Ω
$R_{DS(ON)}$	Drain-Source On-State Resistance③	$V_{GS}=4.5V, I_D=15A$	--	4.5	6.0	m Ω
Dynamic Electrical Characteristics @ $T_j=25^{\circ}\text{C}$ (unless otherwise stated)						
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V,$ $f=1\text{MHz}$	--	2530	--	pF
C_{oss}	Output Capacitance		--	380	--	pF
C_{rss}	Reverse Transfer Capacitance		--	295	--	pF
R_g	Gate Resistance	$f=1\text{MHz}$		0.95		Ω
Q_g	Total Gate Charge	$V_{DS}=15V, I_D=20A,$ $V_{GS}=10V$	--	54	--	nC
Q_{gs}	Gate-Source Charge		--	6	--	nC
Q_{gd}	Gate-Drain Charge		--	14	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=15V,$ $I_D=10A,$ $R_G=3.5\Omega,$ $V_{GS}=10V$	--	8	--	ns
t_r	Turn-on Rise Time		--	5	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	27	--	ns
t_f	Turn-Off Fall Time		--	11	--	ns
Source- Drain Diode Characteristics@ $T_j=25^{\circ}\text{C}$ (unless otherwise stated)						
V_{SD}	Forward on voltage	$I_{SD}=20A, V_{GS}=0V$	--	0.81	1.2	V
t_{rr}	Reverse Recovery Time	$T_j=25^{\circ}\text{C}, I_{sd}=20A,$ $di/dt=500A/\mu s$	--	43	--	ns
Q_{rr}	Reverse Recovery Charge		--	37	--	nC

NOTE:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{jmax} , starting $T_j = 25^\circ\text{C}$, $L = 0.5\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 32A$, $V_{GS} = 10V$. Part not recommended for use above this value
- ③ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

Typical Characteristics

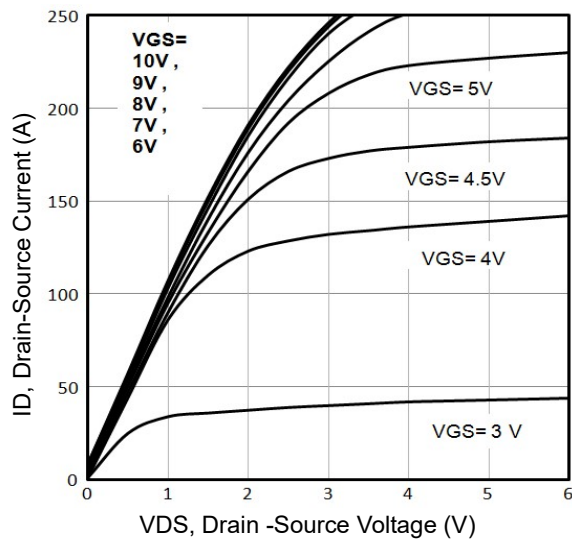


Fig1. Typical Output Characteristics

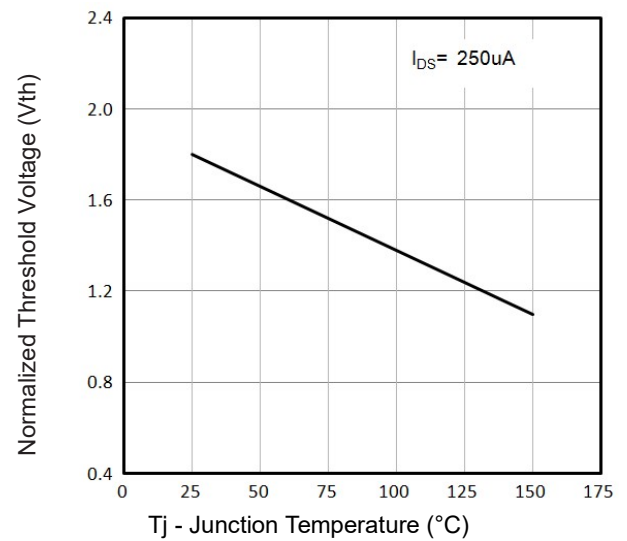


Fig2. $V_{GS(TH)}$ Gate-Source Voltage Vs. T_j

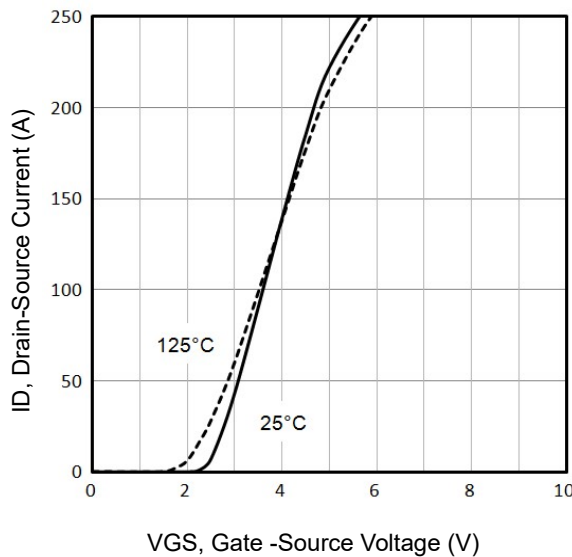


Fig3. Typical Transfer Characteristics

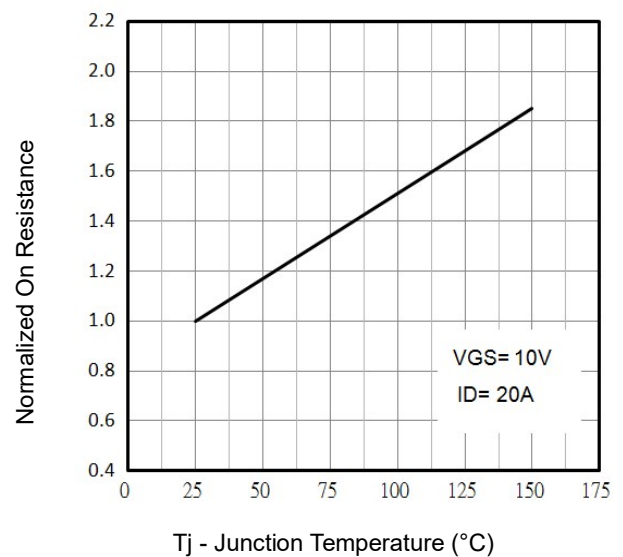


Fig4. Normalized On-Resistance Vs. T_j

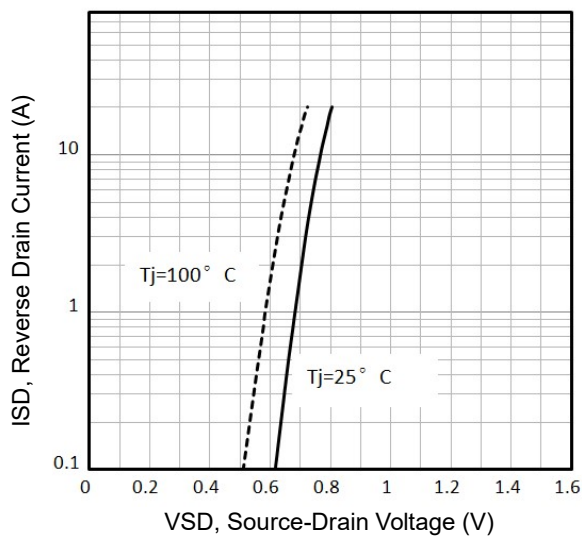


Fig5. Typical Source-Drain Diode Forward Voltage

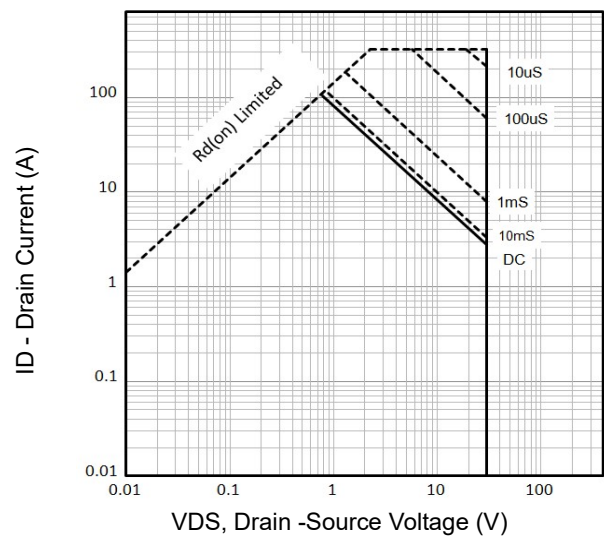


Fig6. Maximum Safe Operating Area

Typical Characteristics

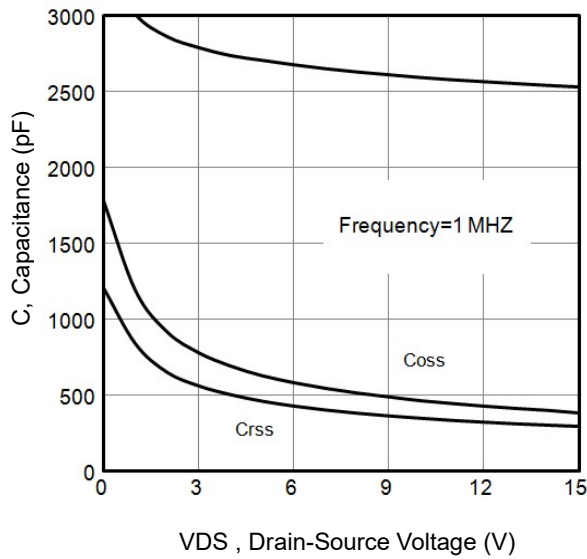


Fig7. Typical Capacitance Vs. Drain-Source Voltage

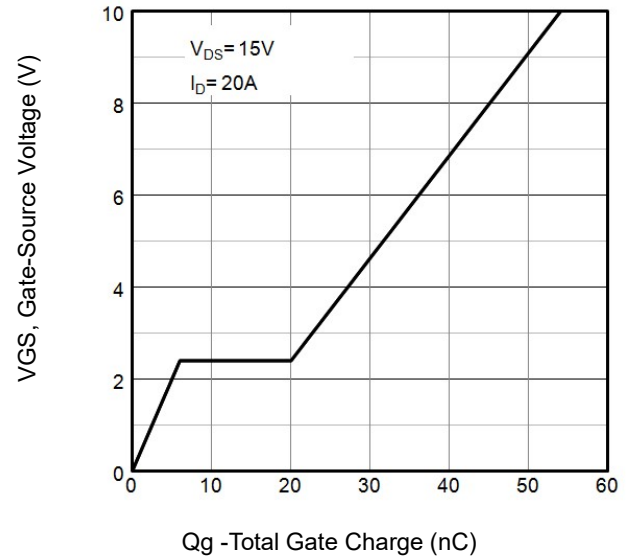


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

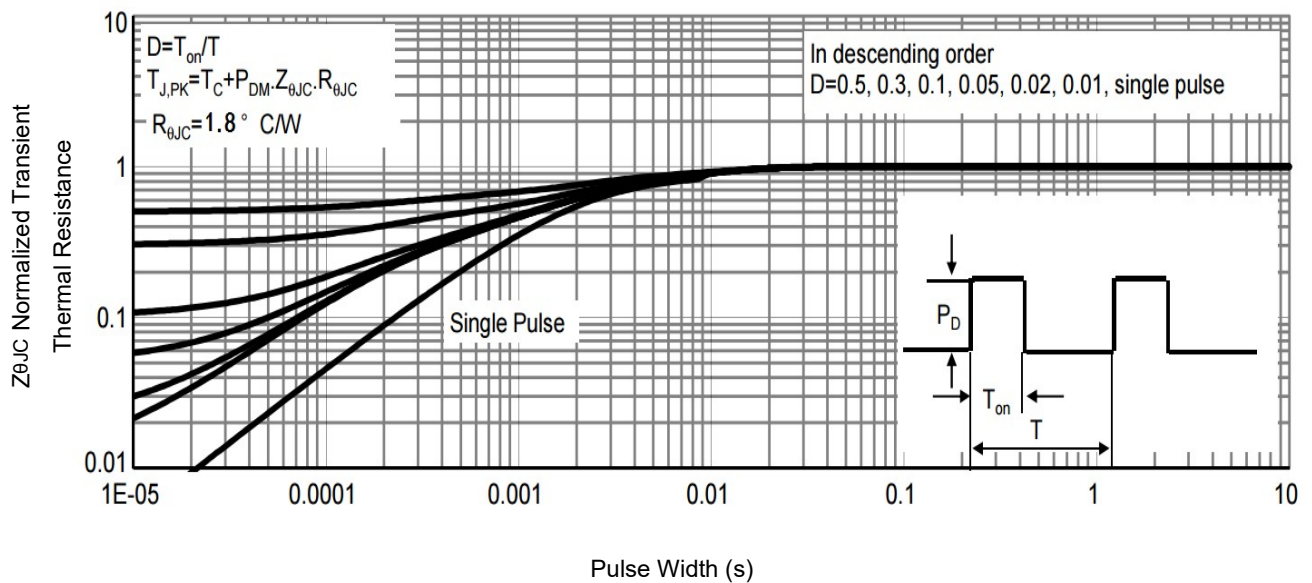


Fig9 . Normalized Maximum Transient Thermal Impedance

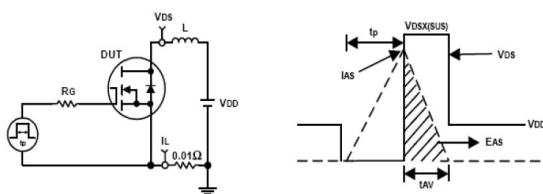


Fig10. Unclamped Inductive Test Circuit and waveforms

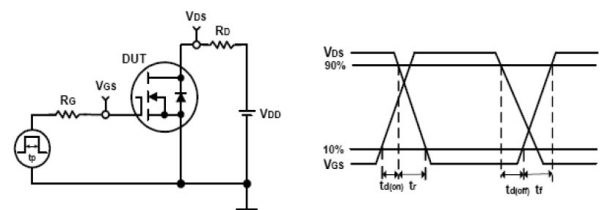
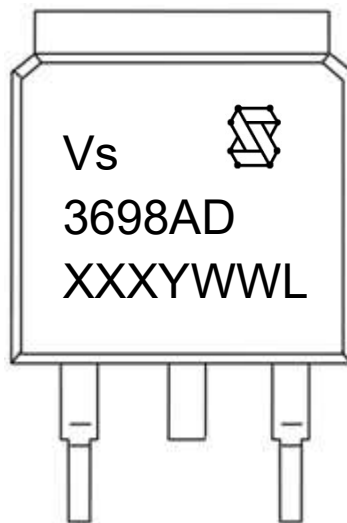


Fig11. Switching Time Test Circuit and waveforms

Marking Information



1st line: Vergiga Code (Vs), Vergiga Logo

2nd line: Part Number (3698AD)

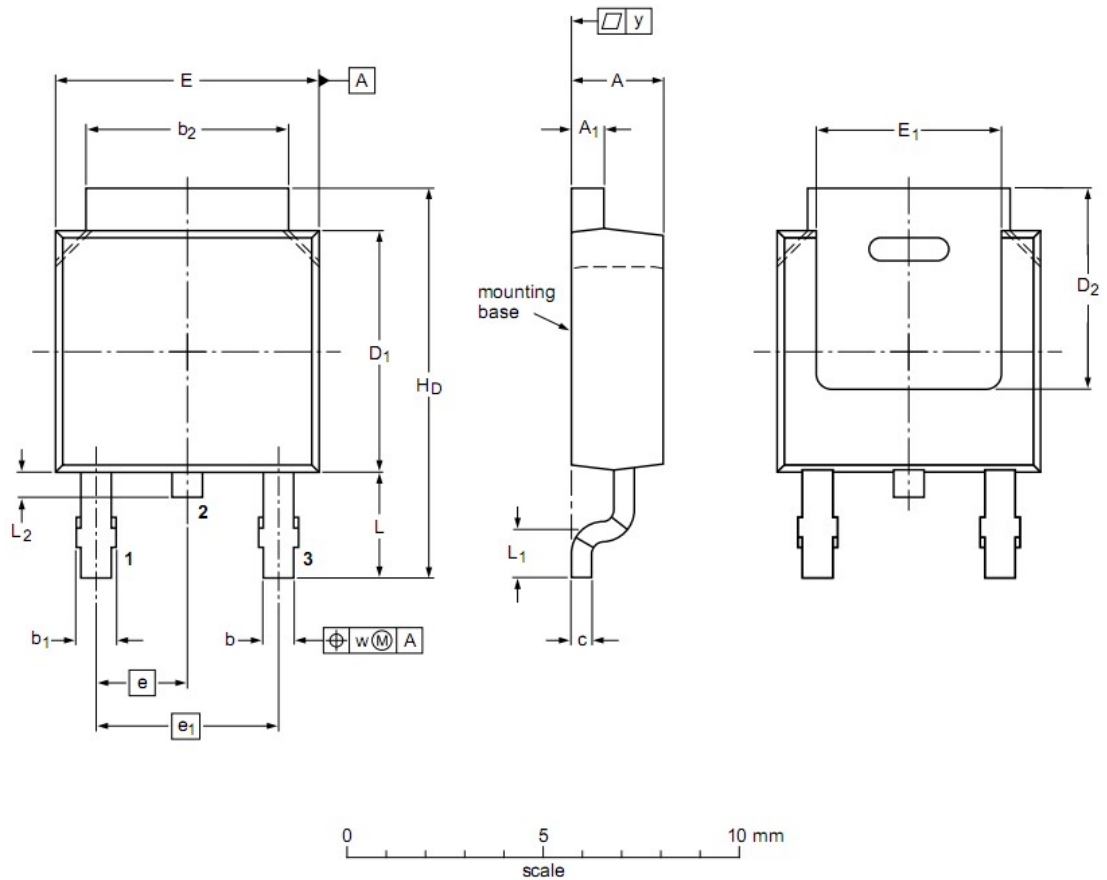
3rd line: Date code (XXXYWWL)

XXX: Wafer Lot Number Code , code changed with Lot Number

Y: Year Code , refer to table below

WW: Week Code (01 to 53)

Code	C	D	E	F	G	H	J	K	L	M	N	P	Q	R	S	T
Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030

TO-252 Package Outline Data


Symbol	Dimensions (unit: mm)		
	Min	Typ	Max
A	2.20	2.30	2.38
A₁	0.46	0.50	0.63
b	0.64	0.76	0.89
b₁	0.77	0.85	1.14
b₂	5.00	5.33	5.46
c	0.458	0.508	0.558
D₁	5.98	6.10	6.223
D₂	5.21	--	--
E	6.40	6.60	6.731
E₁	4.40	--	--
e	2.286 BSC		
e₁	--	4.57	--
H_D	9.40	10.00	10.40
L	2.743 REF		
L₁	1.40	1.52	1.77
L₂	0.50	0.80	1.01
w	--	0.20	--
y	--	--	0.20

Notes:

1. Refer to JEDEC TO-252 variation AA
2. Dimension "E" does NOT include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.1524mm per side.
3. Dimension "D₁" does NOT include interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.1524mm per end.

Customer Service
Sales and Service:
sales@vgsemi.com
Vergiga Semiconductor CO., LTD
TEL: (86-755) -26902410

FAX: (86-755) -26907027

WEB: www.vgsemi.com